

MOSFET – Power, Dual, N-Channel, μ Cool, UDFN6, 2.0x2.0x0.55 mm 30 V, 7.3 A

NTLUD4C26N

Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0 x 2.0 x 0.55 mm for Board Space Saving
- Ultra Low $R_{DS(on)}$
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Load Switch
- Wireless Charging
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	7.3	A
		$T_A = 85^\circ\text{C}$		5.3	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$		9.1	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.70	W
		$T_A = 85^\circ\text{C}$		2.63	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$		2.63	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	4.8	A
		$T_A = 85^\circ\text{C}$		3.4	
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	P_D	0.72	W
Pulsed Drain Current		$t_p = 10$ μ s	I_{DM}	22	A
MOSFET Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 1)			I_S	3.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

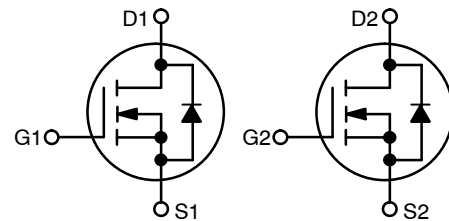


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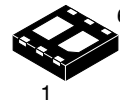
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MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	24 m Ω @ 4.5 V	7.3 A
	65 m Ω @ 1.8 V	

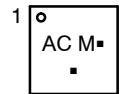


Dual N-Channel MOSFET



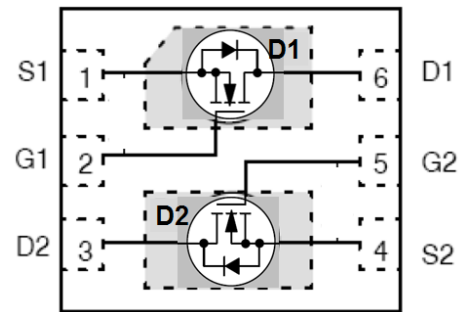
UDFN6
CASE 517BF
 μ COOL™

MARKING DIAGRAM



AC = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

NTLUD4C26N

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	73.6	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	47.6	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	174.4	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface-mounted on FR4 board using the minimum recommended pad size, 2 oz. Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250$ μ A, ref to 25°C		7		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 24$ V	$T_J = 25^\circ\text{C}$		1	μ A
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 12$ V			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μ A	0.6		1.1	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			2.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5$ V, $I_D = 5.0$ A		20	24	m Ω
		$V_{GS} = 1.8$ V, $I_D = 1.0$ A		40	65	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5$ V, $I_D = 5.0$ A		23		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = 15$ V		460		pF
Output Capacitance	C_{OSS}			225		
Reverse Transfer Capacitance	C_{RSS}			27		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 10$ V; $I_D = 5.0$ A		5.0	8.0	nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V; $I_D = 5.0$ A		5.5	9.0	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.55		
Gate-to-Source Charge	Q_{GS}			2.5		
Gate-to-Drain Charge	Q_{GD}			1.1		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DD} = 15$ V, $I_D = 5.0$ A, $R_G = 1$ Ω		5		ns
Rise Time	t_r			15		
Turn-Off Delay Time	$t_{d(OFF)}$			13		
Fall Time	t_f			1.7		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = 2.0$ A	$T_J = 25^\circ\text{C}$		0.7	1.0	V
			$T_J = 125^\circ\text{C}$		0.6		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width ≤ 300 μ s, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTLUD4C26N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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DRAIN-SOURCE DIODE CHARACTERISTICS

Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 2.0 A		18.5		ns
Charge Time	t _a			9.3		
Discharge Time	t _b			9.1		
Reverse Recovery Charge	Q _{RR}			7.8		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

DEVICE ORDERING INFORMATION

Device	Package	Shipping†
NTLUD4C26NTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUD4C26NTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

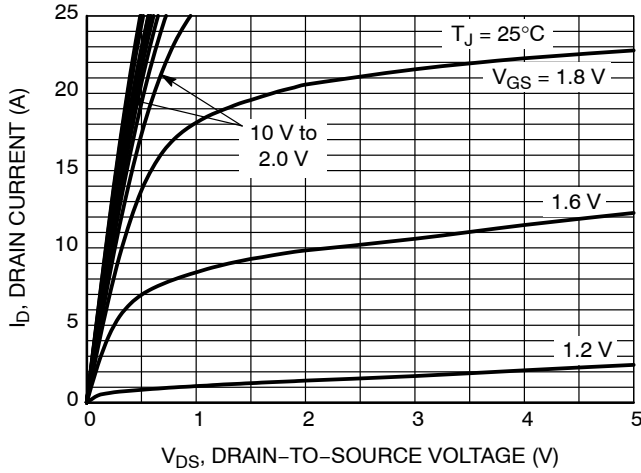


Figure 1. On-Region Characteristics

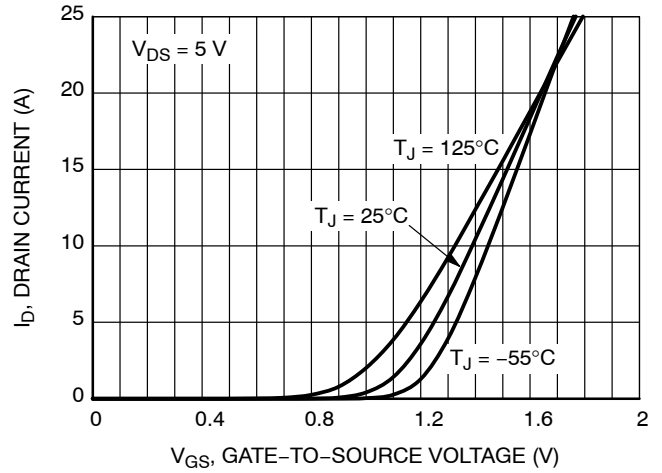


Figure 2. Transfer Characteristics

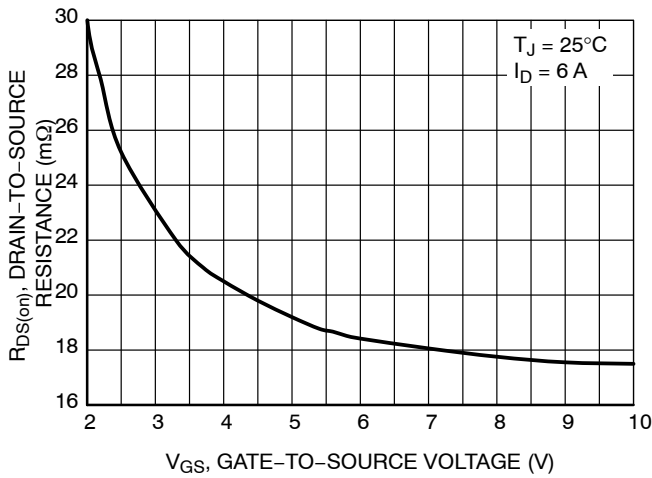


Figure 3. On-Resistance vs. Gate-to-Source Voltage

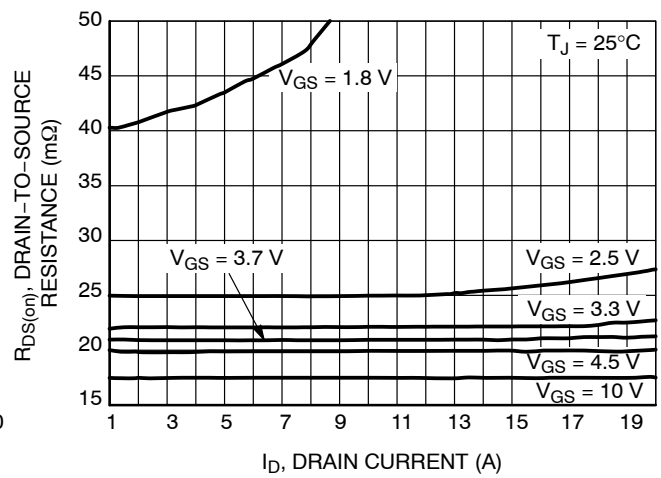


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

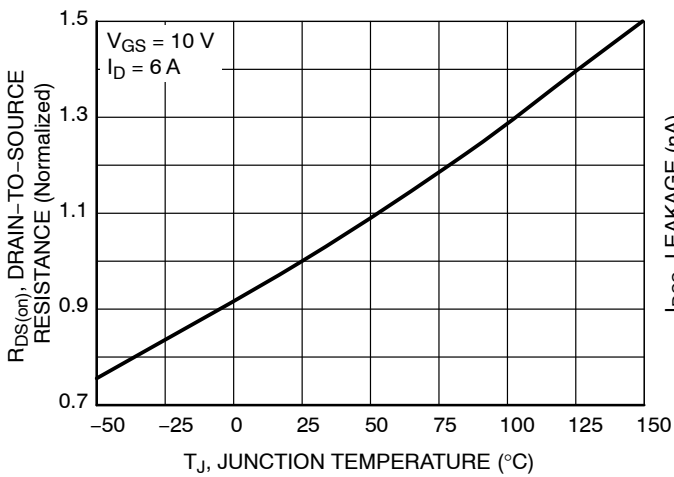


Figure 5. On-Resistance Variation with Temperature

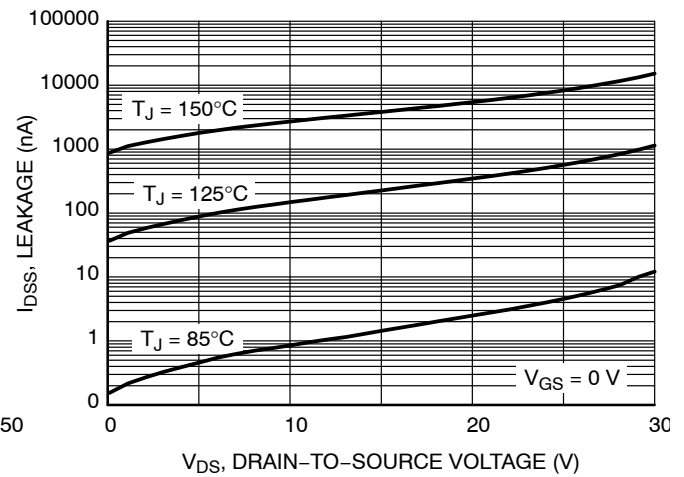


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

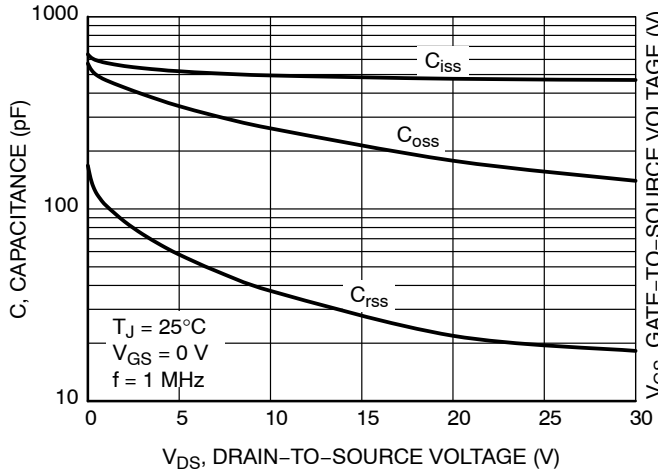


Figure 7. Capacitance Variation

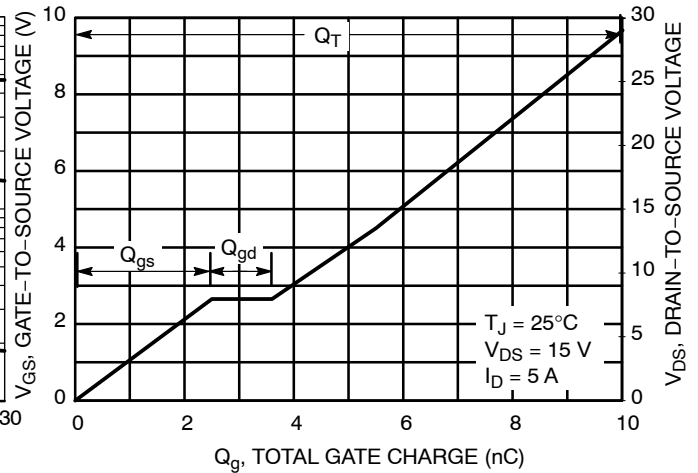


Figure 8. Gate-to-Source vs. Total Charge

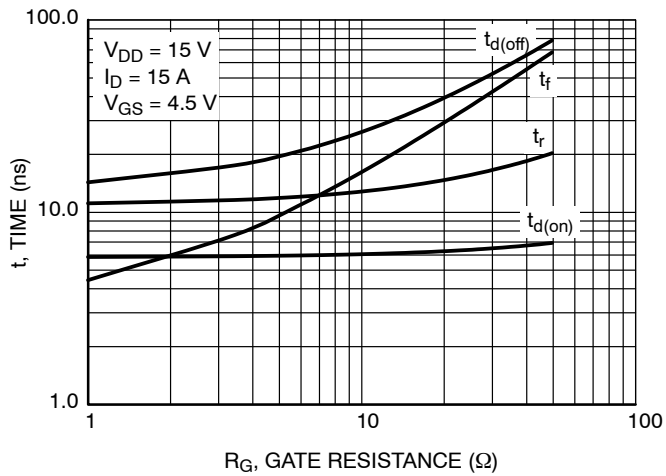


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

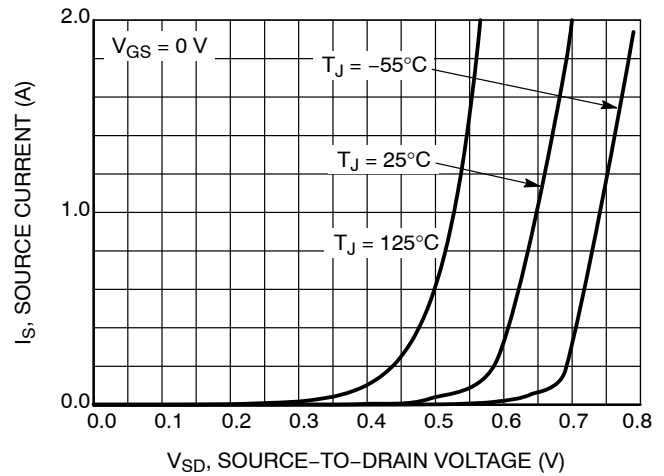


Figure 10. Diode Forward Voltage vs. Current

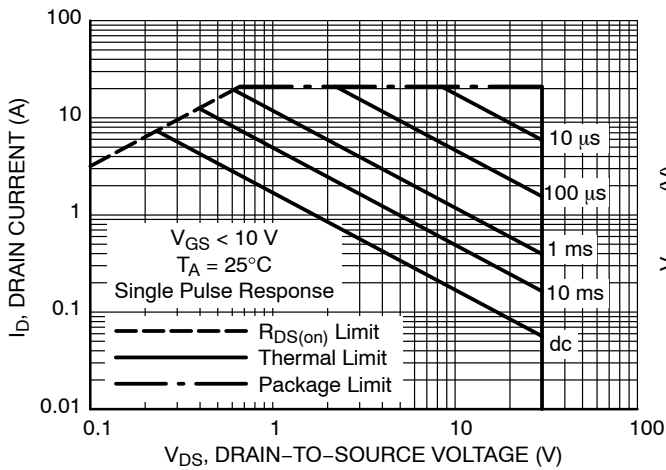


Figure 11. Maximum Rated Forward Biased Safe Operating Area

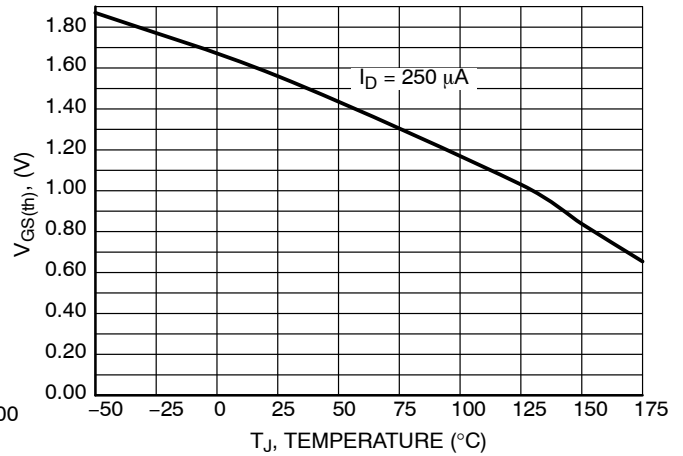


Figure 12. Threshold Voltage

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TYPICAL CHARACTERISTICS

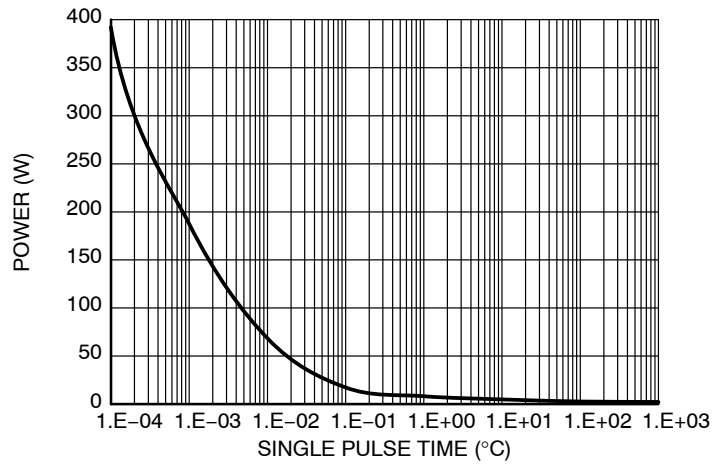


Figure 13. Single Pulse Maximum Power Dissipation

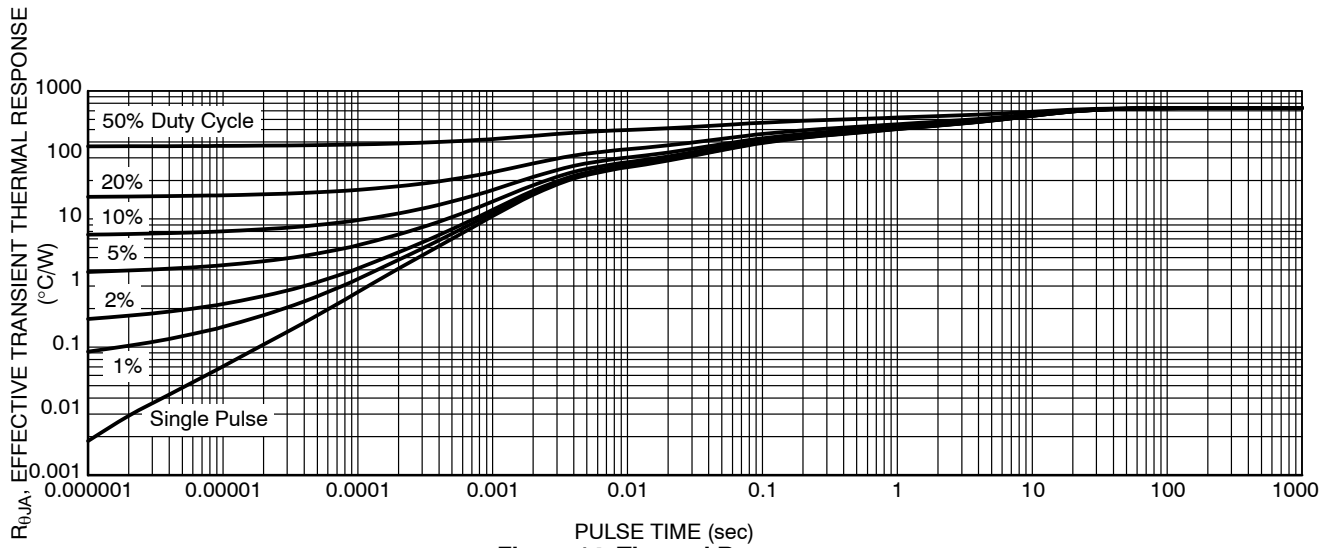
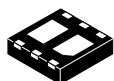


Figure 14. Thermal Response

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

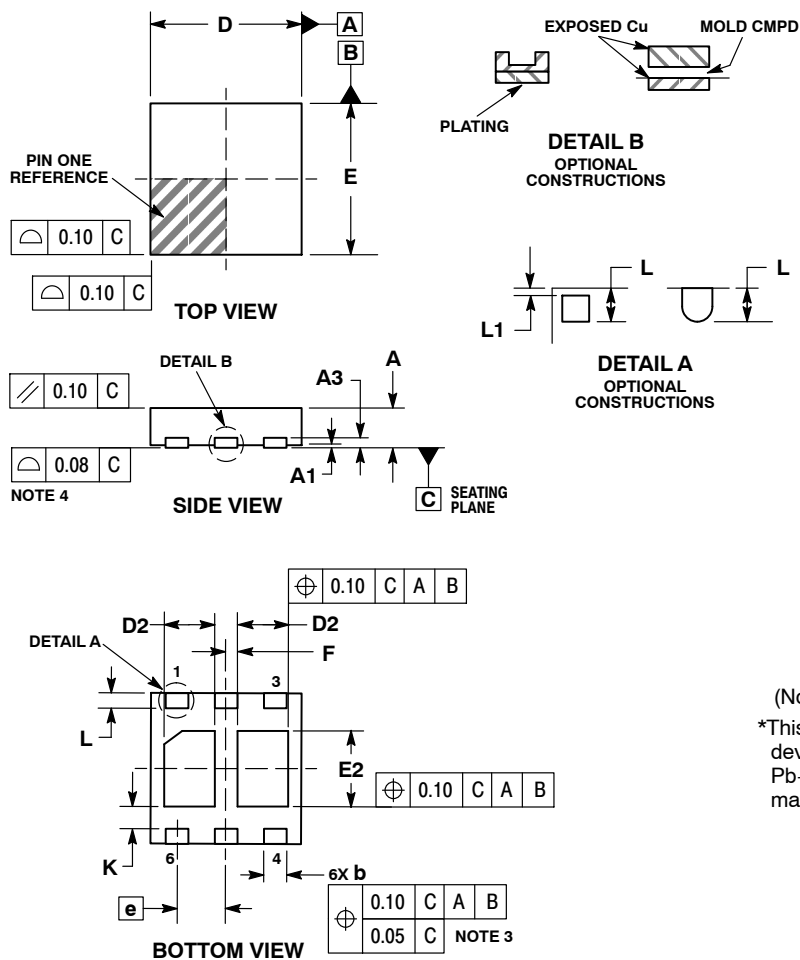
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SCALE 4:1

UDFN6 2x2, 0.65P
CASE 517BF
ISSUE B

DATE 20 AUG 2012



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.25	0.35
D	2.00	BSC
D2	0.57	0.77
E	2.00	BSC
E2	0.90	1.10
e	0.65	BSC
F	0.15	BSC
K	0.25	REF
L	0.20	0.30
L1	---	0.10

GENERIC MARKING DIAGRAM*



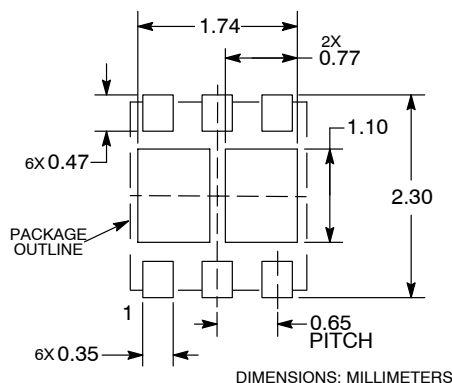
XX = Specific Device Code

M = Date Code

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT



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DESCRIPTION:	UDFN6 2X2, 0.65P	PAGE 1 OF 1

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